## MCH6437





- Low On-Resistance
- 1.8V Drive
- ESD Diode-Protected Gate
- Pb-Free and RoHS Compliance

#### **Specifications**

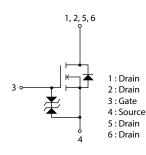
#### Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V <sub>DSS</sub>	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ID	7	А
Drain Current (Pulse) PW≤10µs, duty cycle≤1%	I <sub>DP</sub>	28	А
Power Dissipation When mounted on ceramic substrate (1200mm <sup>2</sup> $\times$ 0.8mm)	PD	1.5	w
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

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VDSS	R <sub>DS</sub> (on) Max	ID Max
	24mΩ@ 4.5V	
20V	35mΩ@ 2.5V	7A
	65mΩ@ 1.8V	

Electrical Connection N-Channel

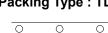


#### Packing Type : TL

#### Marking

#### Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1200mm <sup>2</sup> $\times$ 0.8mm)	R <sub>θJA</sub>	83.3	°C/W



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Fot	71	5
No.	ᆂᄂ	No.
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Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

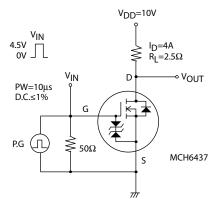
See detailed ordering and shipping information on page 5 of this data sheet.

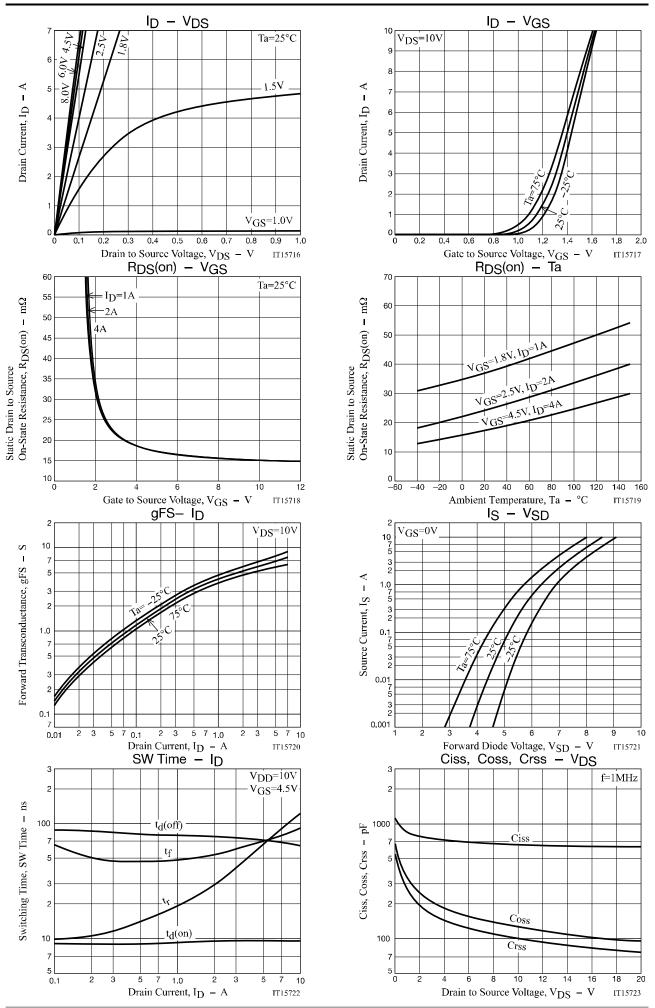
#### **Electrical Characteristics** at $Ta = 25^{\circ}C$

Parameter	Oursels al	Symbol Conditions	Value			11-14
Parameter	Symbol		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =4A		6.2		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =4A, V <sub>GS</sub> =4.5V		18	24	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =2A, V <sub>GS</sub> =2.5V		25	35	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1A, V <sub>GS</sub> =1.8V		38	65	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		660		pF
Output Capacitance	Coss			125		pF
Reverse Transfer Capacitance	Crss			100		рF
Turn-ON Delay Time	t <sub>d</sub> (on)			9.7		ns
Rise Time	tr			53		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		72		ns
Fall Time	tf	1		65		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =7A		8.4		nC
Gate to Source Charge	Qgs			1.0		nC
Gate to Drain "Miller" Charge	Qgd			2.4		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =7A, V <sub>GS</sub> =0V		0.81	1.2	V

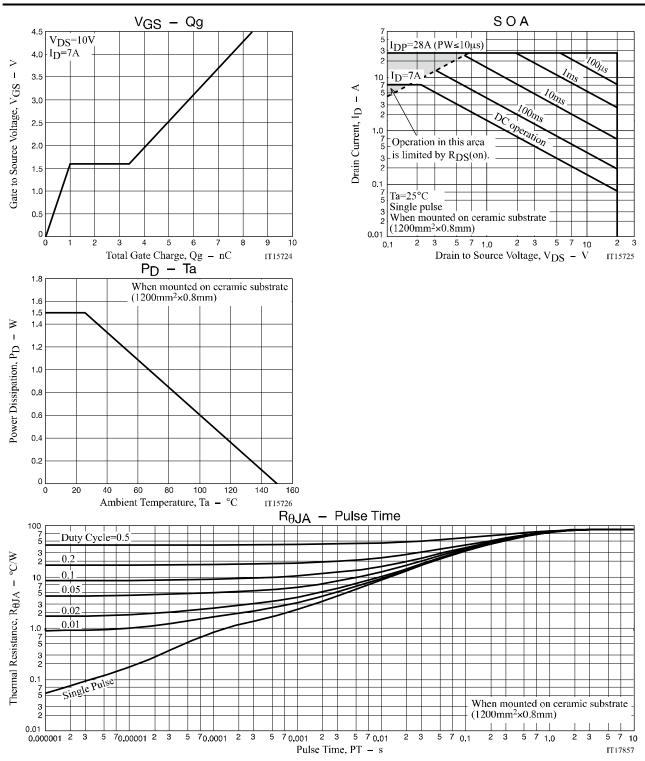
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **Switching Time Test Circuit**





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#### Package Dimensions

MCH6437-TL-E / MCH6437-TL-W

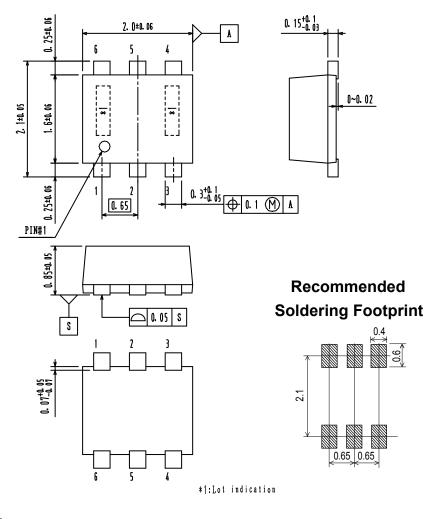
#### MCPH6

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unit : mm

- 1 : Drain
- 2 : Drain
- 3 : Gate
- 4 : Source
- 5 : Drain

6 : Drain



#### **ORDERING INFORMATION**

Device	Package Shipping		Note
MCH6437-TL-E	MCPH6		Pb-Free
MCH6437-TL-W	SC-88FL,SC-70-6,SOT-363	3,000 pcs. / Tape & Reel	Pb-Free and Halogen Free

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

### Note on usage : Since the MCH6437 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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